



제 31회 한국반도체학술대회

The 31st Korean Conference on Semiconductors

2024년 1월 24일(수)-26일(금) | 경주화백컨벤션센터(HICO)

2024년 1월 26일(금), 13:45-15:30

Room H(202), 2층

K. Memory (Design & Process Technology) 분과

[FH2-K] Ferroelectric Memory I

좌장: 권용우 교수(홍익대학교), 정성엽 박사(차세대융합기술연구원)

<p>FH2-K-1 13:45-14:00</p>	<p>Effect of Al Dopant Distribution in HfO₂ Layer on Ferroelectric Switching Characteristics Hyoungjin Park¹, Seonuk Jeon², Hyun Wook Kim², Eunryeong Hong², Nayeon Kim², Yunsur Kim¹, Hyeonsik Choi¹, Jiae Jeong¹, and Jiyong Woo^{1,2} ¹School of Electronic Engineering, Kyungpook National University, ²School of Electronic and Electrical Engineering, Kyungpook National University</p>
<p>FH2-K-2 14:00-14:15</p>	<p>Novel Dual Ferroelectric Stack with Wide-range Tunable Coercive Voltage for High-density 3D FeNAND Applications Jiae Jeong¹, Nayeon Kim², Hyunwook Kim², Eunryeong Hong², Seonuk Jeon², Yunsur Kim¹, Hyeonsik Choi¹, Hyoungjin Park¹, and Jiyong Woo^{1,2} ¹School of Electronic Engineering, Kyungpook National University, ²School of Electronic and Electrical Engineering, Kyungpook National University</p>
<p>FH2-K-3 14:15-14:30</p>	<p>La₂O₃ 중간층을 이용한 Ferroelectric FET 의 성능 및 내구성 개선 강창연, 추준홍, 김성호, 박영근, 김승훈, 조병진 한국과학기술원 전기 및 전자공학부</p>
<p>FH2-K-4 14:30-14:45</p>	<p>Enhancing Non-Volatile Memory Performance: Dual Ferroelectric Gate Field-Effect Transistors with Recessed Channel Geometry Simin Chen¹, Dae-Hwan An², Seong Ui An¹, Tae Hyeon Noh¹, and Younghyun Kim¹ ¹Department of Photonics and Nanoelectronics, BK21 FOUR ERICA-ACE Center, Hanyang University, ²Center for Opto-electronic Materials and Devices, KIST</p>
<p>FH2-K-5 14:45-15:00</p>	<p>Demonstration of Programmable Low-Temperature Hf-Based Ferroelectric Amorphous Oxide Semiconductor FET for Emerging Memory Applications Tae Hyeon Noh¹, Dae-Hwan Ahn², Hyo-Bae Kim³, Taewon Jin¹, Seoung min Park¹, Seong Ui An¹, Xinkai Sun¹, Simin Chen¹, Ji-Hoon Ahn³, and Younghyun Kim¹ ¹Department of Photonics and Nanoelectronics, BK21 FOUR ERICA-ACE Center, Hanyang University, ²Center for Opto-electronic Materials and Devices, KIST, ³Department of Materials Science and Chemical Engineering, Hanyang University</p>



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FH2-K-6 15:00-15:15	Analysis of Hydrogen Effect on Ferroelectric (Hf,Zr)O ₂ Thin Films during Atomic Layer Deposition Process Seongbin Park ¹ , Seungbin Lee ¹ , Hye Ryeon Park ¹ , Jongmug Kang ¹ , Juntak Jeong ¹ , Yeseo Choi ¹ , Jin-Hyun Kim ² , Minjong Lee ² , Jiyoung Kim ² , and Si Joon Kim ¹ ¹ Kangwon National University, ² The University of Texas at Dallas
FH2-K-7 15:15-15:30	The Effect of Oxygen Vacancy Layer on Memory Performance of Hafnia Ferroelectric Tunnel Junction Junghyeon Hwang, Chaeheon Kim, Hunbeom Shin, and Sanghun Jeon School of Electrical Engineering, KAIST